



SEMICONDUCTOR

SS8050LT1

Shandong Yiguang Electronic Joint stock Co., Ltd

TECHNICAL DATA

NPN EPITAXIAL SILICON TRANSISTOR

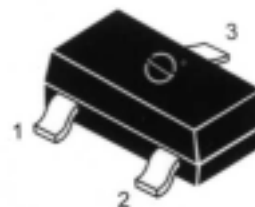
2W OUTPUT AMPLIFIER OF PORTABLE**RADIOS IN CLASS****B PUSH-PULL OPERATION**

- * Complement to SS8550LT1
- * Collector Current :Ic= 800mA
- * High Total Power Dissipation :Pc=625mW

ABSOLUTE MAXIMUM RATINGS at Ta=25

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	40	V
Collector-Emitter Voltage	Vceo	25	V
Emitter-Base Voltage	Veb	6	V
Collector Current	Ic	800	mA
Collector Dissipation Ta=25 *	P _D	625	mW
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-55-150	

Package:SOT-23



PIN:	1	2	3
STYLE			
NO.1	B	E	C

ELECTRICAL CHARACTERISTICS at Ta=25

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BVcbo	40			V	Ic=100uA Ie=0
Collector-Emitter Breakdown Voltage#	BVceo	25			V	Ic= 1mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	6			V	Ie= 100uA Ic=0
Collector Cutoff Current	Icbo			100	nA	Vcb= 40V Ie=0
Emitter Cutoff Current	Iceo			100	nA	Vce=20 V Ie=0
Emitter Cutoff Current	Iebo			100	nA	Veb=5V Ic=0
DC Current Gain	Hfe ₁	120		350		Vce= 1V Ic= 100mA
DC Current Gain	Hfe ₂	40				Vce= 1V Ic= 800mA
Collector-Emitter Saturation Voltage	Vce(sat)			0.6	V	Ic= 800mA Ib= 80mA
Base-Emitter Saturation Voltage	Vbe(sat)			1.2	V	Ic= 800mA Ib= 80mA
Current Gain-Bandwidth Product	f _T	100			MHz	Vce=10V Ic=50mA f=30MHz

* Total Device Dissipation : FR=1x0.75x0.062in Board,Derate 25 .

Pulse Test : Pulse Width 300uS,Duty cycle 2%

CLASSIFICATION OF Hfe₍₁₎

Rank	L	H
Range	120—200	200—350

DEVICE MARKING:

SS8050LT1=Y1



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